Description

JMT Dual P-channel Enhancement Mode Power MosFET

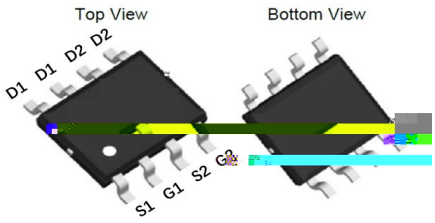
Features

-30V, -5.1A
$R_{DS(ON)}$ < 43m V_{GS} = -10V
$R_{DS(ON)}$ < 64m V_{GS} = -4.5V
Advanced Trench Technology
Excellent $R_{DS(ON)}$ and Low Gate Charge
Lead Free

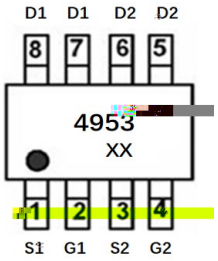
Applications

Load Switch
PWM Application
Power Management

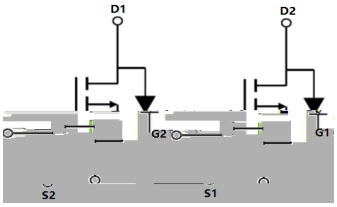
100% UIS TESTED!
100% ΔVds TESTED!



SOP-8



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

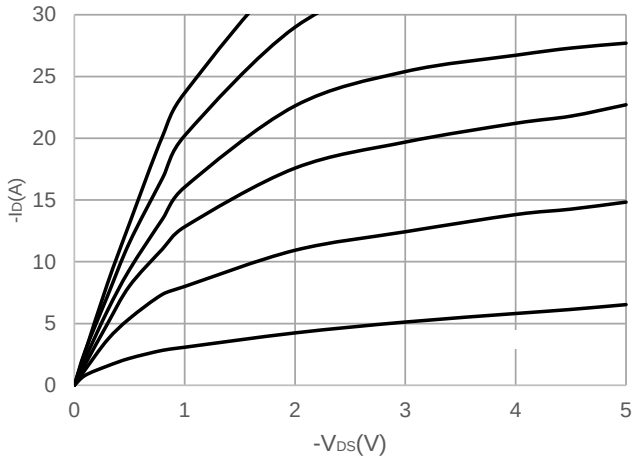
Device Marking	Device	Outline	Package	Reel Size		
4953	JMTP4953A		SOP-8			

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

I_D	Parameter	Value	A
	Drain-to-Source Voltage	-30	
	Gate-to-Source Voltage	±20	
			°C

Typical Performance Characteristics

Figure 1: Output Characteristics



Test Circuit

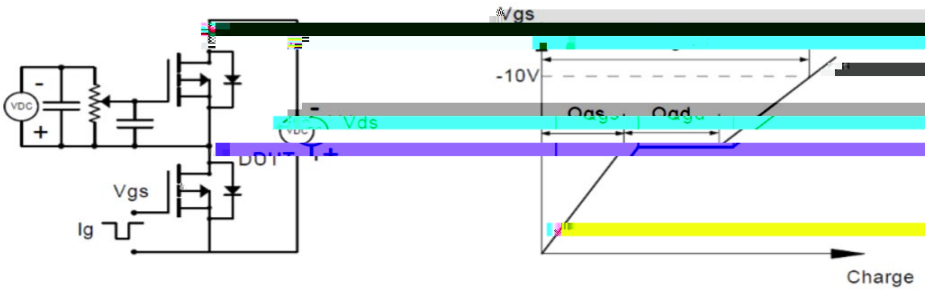


Figure 1: Gate Charge Test Circuit & Waveform

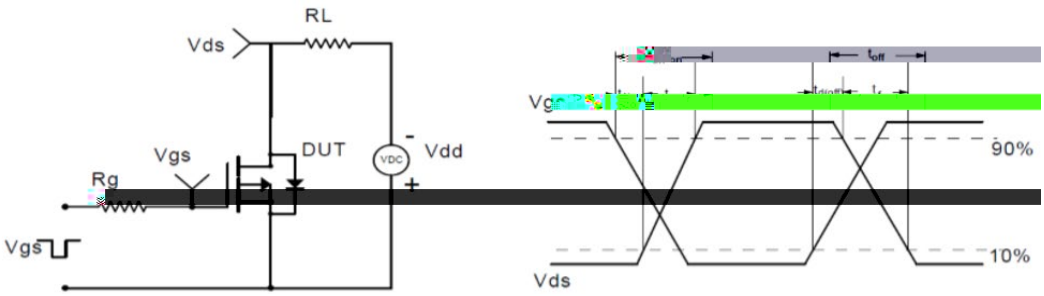


Figure 2: Resistive Switching Test Circuit & Waveform

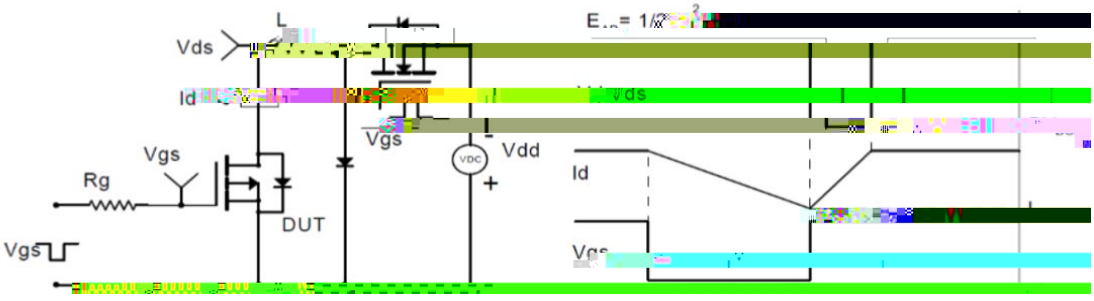


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

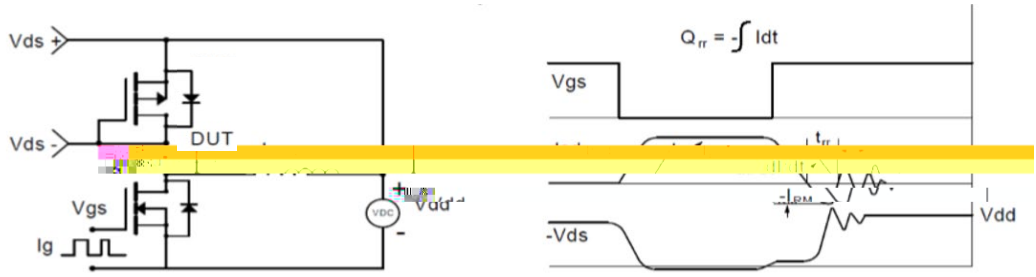
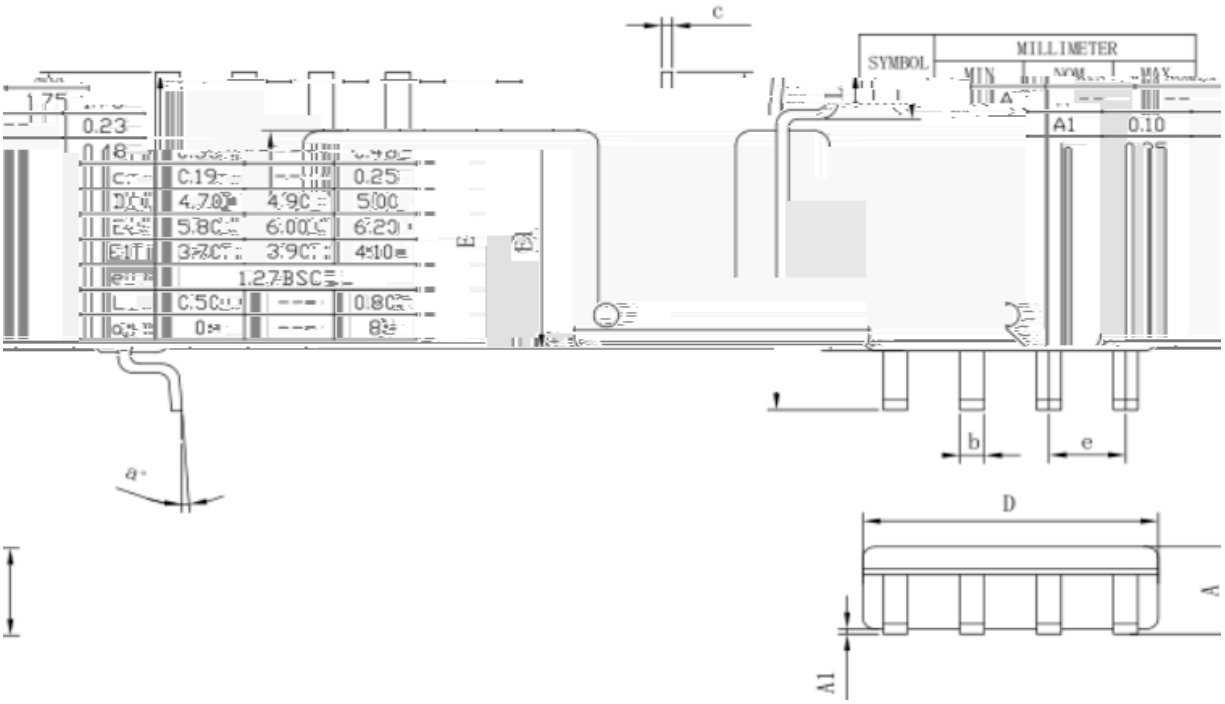


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOP-8)



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